

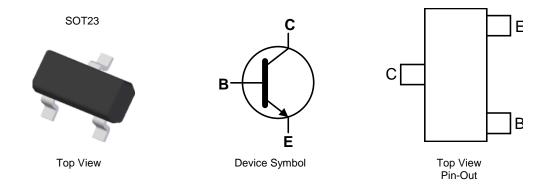
60V NPN MEDIUM POWER TRANSISTOR IN SOT23

Features

- BV_{CEO} > 60V
- BV_{CEX} > 150V
- BV_{ECO} > 6V
- I_C = 3.5A high Continuous Collector Current
- V_{CE(SAT)} < 65mA @1A
- $R_{CE(SAT)} = 43m\Omega$ @1A
- 1.25W Power Dissipation
- Complementary PNP Type: ZXTP25060BFH
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- UL Flammability Rating 94V-0
- Case Material: Molded Plastic. "Green" Molding Compound.
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (Approximate)



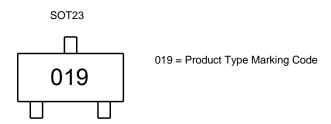
Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXTN25060BFHTA	AEC-Q101	019	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





Absolute Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	150	V
Collector-Emitter Voltage (Forward Blocking)	V _{CEX}	150	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Collector Voltage (Reverse Blocking)	V _{ECO}	6	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	lc	3.5	Α
Peak Pulse Current	Ісм	10	Α
Base Current	lΒ	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) Linear Derating Factor	P _D	0.73 5.84	W mW/°C
Power Dissipation (Note 6) Linear Derating Factor	P _D	1.05 8.4	W mW/°C
Power Dissipation (Note 7) Linear Derating Factor	P _D	1.25 9.6	W mW/°C
Power Dissipation (Note 8) Linear Derating Factor	P _D	1.81 14.5	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	171	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	119	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	R _{θJA}	100	°C/W
Thermal Resistance, Junction to Ambient (Note 8)	R _{θJA}	69	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

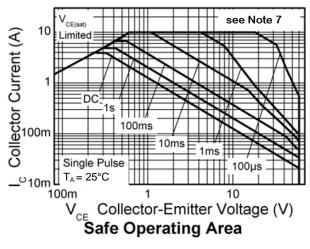
Notes:

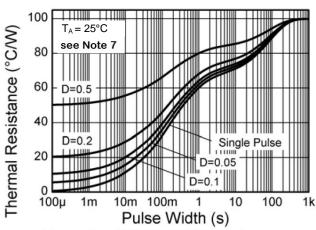
- 5. For a device surface mounted on 15mm X 15mm X 1.6mm FR-4 PCB with high coverage of single sided 1 oz copper, in still air conditions.
- 6. Mounted on 25mm X 25mm X 1.6mm FR-4 PCB with high coverage of single sided 2 oz copper, in still air conditions.

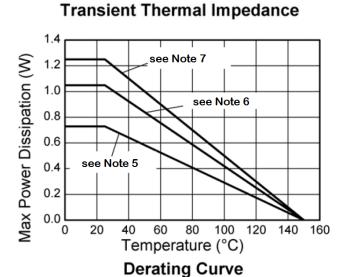
 7. Mounted on 50mm X 50mm X 1.6mm FR-4 PCB with high coverage of single sided 2 oz copper, in still air conditions.
- 8. As (7) above measured at t<5s.
- 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

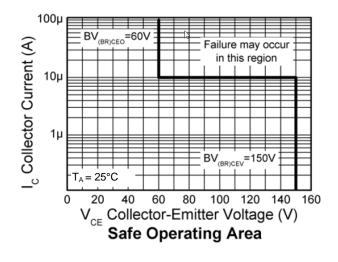


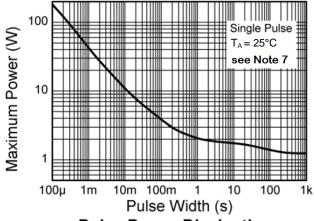
Thermal Characteristics and Derating Information











Pulse Power Dissipation



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

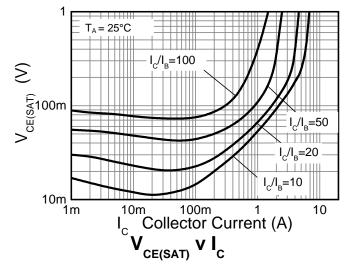
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	150	190	_	V	$I_{C} = 100 \mu A$
Collector Emitter Breakdown Voltage (Forward Blocking)	BV _{CEX}	150	190	_	V	I_C = 100μA, $R_{BE} \le 1$ k Ω or -1V < V _{BE} < 0.25V
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	60	80	_	V	I _C = 10mA
Emitter-Collector Breakdown Voltage (Reverse Blocking)	BV_{ECX}	6	8	_	V	$I_E = 100\mu A$, $R_{BE} \le 1k\Omega$ or -1V < V _{BC} < 0.25V
Emitter-Collector Breakdown Voltage (Base Open)	BV _{ECO}	6	7	_	V	$I_{E} = 100 \mu A$
Emitter-Base Breakdown Voltage	BV_{EBO}	7	8	_	V	$I_{E} = 100 \mu A$
Collector Cutoff Current	I _{CBO}	_	<1 —	50 20	nΑ μΑ	V _{CB} = 120V V _{CB} = 120V, T _A = +100°C
Collector Emitter Cutoff Current	I _{CEX}	_	_	100	nA	V_{CE} = 120V, R_{BE} ≤ 1k Ω or -1V < V_{BE} < 0.25V
Emitter Cutoff Current	I _{EBO}	_	<1	50	nA	V _{EB} = 5.6V
Static Forward Current Transfer Ratio (Note 10)	h _{FE}	100 90 25	200 180 40	300 _ _	_	$I_{C} = 10 \text{mA}, V_{CE} = 2 \text{V}$ $I_{C} = 1 \text{A}, V_{CE} = 2 \text{V}$ $I_{C} = 3.5 \text{A}, V_{CE} = 2 \text{V}$
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(SAT)}	_	33 73 50 150	40 95 65 175	mV mV mV	$\begin{split} I_C &= 0.5 \text{A}, \ I_B = 50 \text{mA} \\ I_C &= 0.5 \text{A}, \ I_B = 10 \text{mA} \\ I_C &= 1 \text{A}, \ I_B = 100 \text{mA} \\ I_C &= 3.5 \text{A}, \ I_B = 350 \text{mA} \end{split}$
Base-Emitter Turn-On Voltage (Note 10)	$V_{BE(ON)}$	_	865	950	mV	$I_C = 3.5$ mA, $V_{CE} = 2$ V
Base-Emitter Saturation Voltage (Note 10)	$V_{BE(SAT)}$	_	960	1050	mV	$I_C = 3.5$ mA, $I_B = 350$ mA
Output Capacitance (Note 10)	C_obo		11.5	20	pF	V _{CB} = 10V, f = 1MHz
Transition Frequency	f _T		185	_	MHz	$V_{CE} = 5V, I_{C} = 100mA,$ f = 100MHz
Turn-On Time	t _{ON}	_	34	_	ns	V _{CC} =10V, I _C = 500mA
Turn-Off Time	t _{OFF}	_	566	_	ns	$I_{B1} = -I_{B2} = 50 \text{mA}$

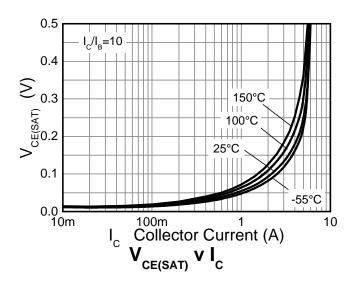
Note:

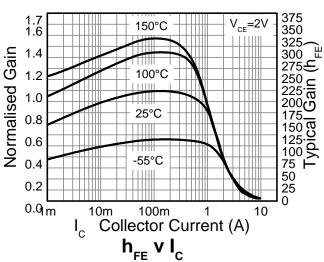
10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

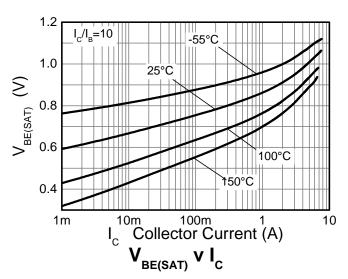


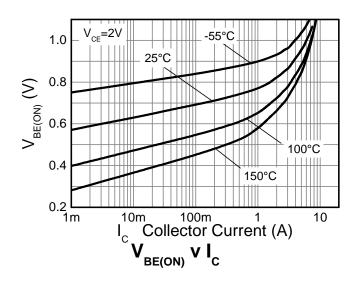
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)









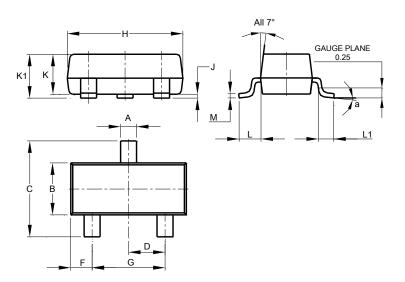




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

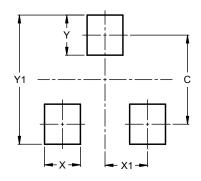


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°	_			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)		
С	2.0		
Х	0.8		
X1	1.35		
Y	0.9		
Y1	2.9		



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